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## **FDD7N20TM N-Channel UniFET<sup>TM</sup> MOSFET** 200 V, 5 A, 690 mΩ

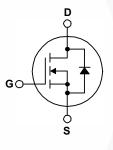
### Features

- $R_{DS(on)}$  = 580 m $\Omega$  (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 2.5 A
- Low Gate Charge (Typ. 5 nC)
- Low C<sub>rss</sub> (Typ. 5 pF)
- 100% Avalanche Tested
- RoHS Compliant

### Applications

- LCD/LED/PDP TV
- Consumer Appliances
- Lighting
- Uninterruptible Power
- AC-DC Power Supply





UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage

MOSFET family based on planar stripe and DMOS technology.

This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche en-

ergy strength. This device family is suitable for switching power

converter applications such as power factor correction (PFC),

flat panel display (FPD) TV power, ATX and electronic lamp bal-

Description

lasts.

### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FDD7N20TM	Unit	
V <sub>DSS</sub>	Drain to Source Voltage		200	V	
V <sub>GSS</sub>	Gate to Source Voltage		±30	V	
ID	DrainCurrent	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		5	Α
		- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C)		3	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	15	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	62.5	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	5	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	4.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation	$(T_{\rm C} = 25^{\rm o}{\rm C})$		43	W
		- Derate Above 25°C		0.34	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Seco	onds	300	°C

### **Thermal Characteristics**

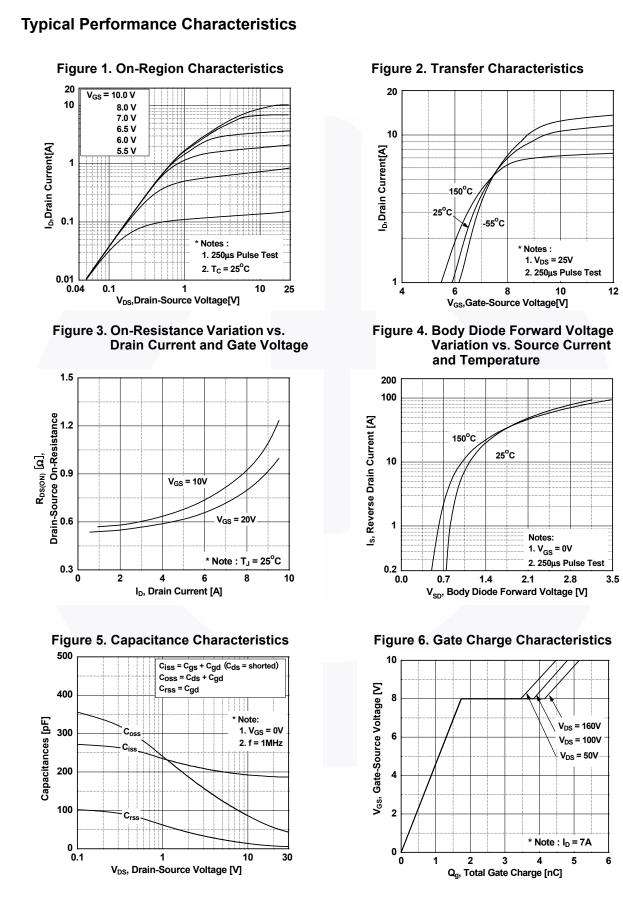
Symbol	Parameter	FDD7N20TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.9	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	110	°C/W

November 2013

FDD7N20TM
— N-Channel
UniFET <sup>TM</sup> N
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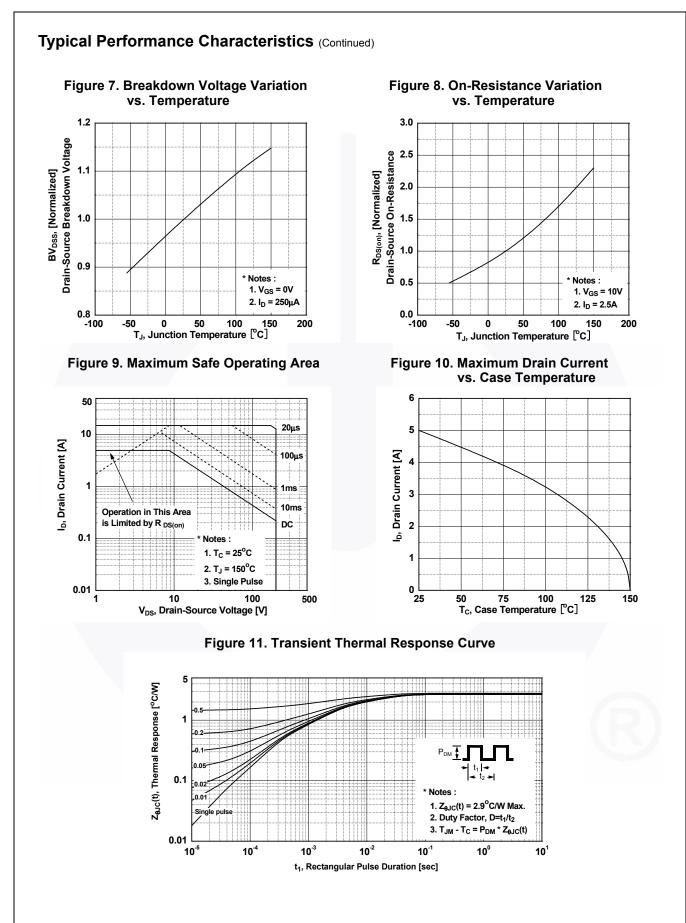
TM FDD7N2	rk	Package	Packing Method	Reel Size	) Та	ape Width	Qu	antity
		DPAK	Tape and Reel	330 mm		16 mm	2500 units	
Characteristics	T <sub>C</sub> = 25°C	unless othe	rwise noted.	I	1			
Paramete	-		Test Condition	าร	Min.	Тур.	Max.	Unit
eristics				<u>`</u>				
Drain to Source Breakdov	wn Voltage	I <sub>D</sub> =	250 μA, V <sub>GS</sub> = 0 V,	T <sub>.1</sub> = 25 <sup>o</sup> C	200	-	-	V
V <sub>DSS</sub> Drain to Source Breakdown Voltage     BV <sub>DSS</sub> Breakdown Voltage Temperature     ΔT <sub>J</sub> Coefficient			$I_D = 250 \ \mu\text{A}, \text{ Referenced to } 25^{\circ}\text{C}$		-	0.2	-	V/ºC
		-			-	-	1	μA
<b>.</b>				)	-	-	10	μA
Gate to Body Leakage Current		V <sub>GS</sub>	$s = \pm 30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$		-	-	±100	nA
ristics								
Gate Threshold Voltage		V <sub>GS</sub>	<sub>S</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
Static Drain to Source On	Resistance				-	0.58	0.69	Ω
Forward Transconductan	се	V <sub>DS</sub>	<sub>s</sub> = 40 V, I <sub>D</sub> = 2.5 A		-	6.2	-	S
aracteristics								
				-	185	250	pF	
				_	_			pF
	ance	f = ′	1 MHz	_	-	5		pF
		N (	400.1/1 7.4		-	5	6.7	nC
		V <sub>DS</sub> = 160 V, I <sub>D</sub> = 7 A, V <sub>CS</sub> = 10 V		-	1.7	-	nC	
Gate to Drain "Miller" Cha	irge				-	2.4	-	nC
haractoristics				k		t		
						9	28	ns
,		Vor	$V_{DD} = 100 \text{ V}, \text{ I}_D = 7 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_G = 25 \Omega$ (Note 4)					ns
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,					-			ns
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		<u> </u>				,		+
					-	-		A
					-	-		A
	ward Voltag					-	1.4	V
-				_			· ·	ns μC
	Drain to Source Breakdow Breakdown Voltage Temp Coefficient Zero Gate Voltage Drain ( Gate to Body Leakage Cu ristics Gate Threshold Voltage Static Drain to Source On Forward Transconductance aracteristics nput Capacitance Dutput Capacitance Reverse Transfer Capacit Total Gate Charge at 10V Gate to Source Gate Cha Gate to Drain "Miller" Cha Bate to Drain "Miller" Cha Gate to Drain "Miller" Cha Gate to Drain "Miller" Cha Gate to Drain "Miller" Cha Gate to Drain "Miller" Cha Curn-On Delay Time Furn-On Rise Time Furn-Off Fall Time Curn-Off Fall Time	Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate to Body Leakage Current <b>ristics</b> Gate Threshold Voltage Static Drain to Source On Resistance Forward Transconductance <b>aracteristics</b> nput Capacitance Dutput Capacitance Reverse Transfer Capacitance Total Gate Charge at 10V Gate to Source Gate Charge Gate to Drain "Miller" Charge haracteristics Furn-On Delay Time Furn-On Rise Time Furn-Off Delay Time Furn-Off Fall Time <b>b Diode Characteristics</b> Maximum Continuous Drain to Source Maximum Pulsed Drain to Source Dio Drain to Source Diode Forward Voltage	Drain to Source Breakdown Voltage ID   Breakdown Voltage Temperature ID   Coefficient ID   Zero Gate Voltage Drain Current VDS   Gate to Body Leakage Current VGS   ristics ID   Gate Threshold Voltage VGS   Static Drain to Source On Resistance VGS   Forward Transconductance VDS   Dutput Capacitance VDS   Dutput Capacitance VDS   Reverse Transfer Capacitance VGS   Gate to Source Gate Charge VGS   Gate to Drain "Miller" Charge VGS   Haracteristics VDS   Furn-On Delay Time VDS   Furn-On Rise Time VGS   Furn-Off Fall Time VGS   Maximum Continuous Drain to Source Diode Forward VGS   Maximum Pulsed Drain to Source Diode Forward VGS   Reverse Recovery Time VGS	Drain to Source Breakdown Voltage $I_D = 250 \ \mu$ A, $V_{GS} = 0 \ V$ , $I_D = 250 \ \mu$ A, ReferencedBreakdown Voltage Temperature Coefficient $I_D 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$V_{DS} = 0 \ V, \ R_G = 25 \ \Omega$ Aximum Continuous Drain to Source Diode Forward CurrentAximum Pulsed Drain to Source Diode Forward CurrentAximum Pulsed Drain to Source Diode Forward CurrentOrain to Source Diode Forward Voltage $V_{GS} = 0 \ V, \ I_{SD} = 5 \ A$ Reverse Recovery Time $V_{GS} = 0 \ V, \ I_{SD} = 7 \ A, \ V_{GS} = 0 \ V, \ I_{SD} = 7 $	Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient $I_D = 250 \ \mu A, \ V_{GS} = 0 \ V, \ T_J = 25^{\circ}C$ $I_D = 250 \ \mu A, \ Referenced to 25^{\circ}C$ $I_D = 250 \ \mu A, \ Referenced to 25^{\circ}C$ Zero Gate Voltage Drain Current $V_{DS} = 200 \ V, \ V_{GS} = 0 \ V$ Gate to Body Leakage Current $V_{GS} = 200 \ V, \ V_{GS} = 0 \ V$ Fistics $V_{GS} = 100 \ V, \ T_C = 125^{\circ}C$ Gate Threshold Voltage $V_{GS} = 40 \ V, \ I_D = 2.5 \ A$ Forward Transconductance $V_{DS} = 40 \ V, \ I_D = 2.5 \ A$ Forward Transconductance $V_{DS} = 40 \ V, \ I_D = 2.5 \ A$ Poutput Capacitance $V_{DS} = 25 \ V, \ V_{GS} 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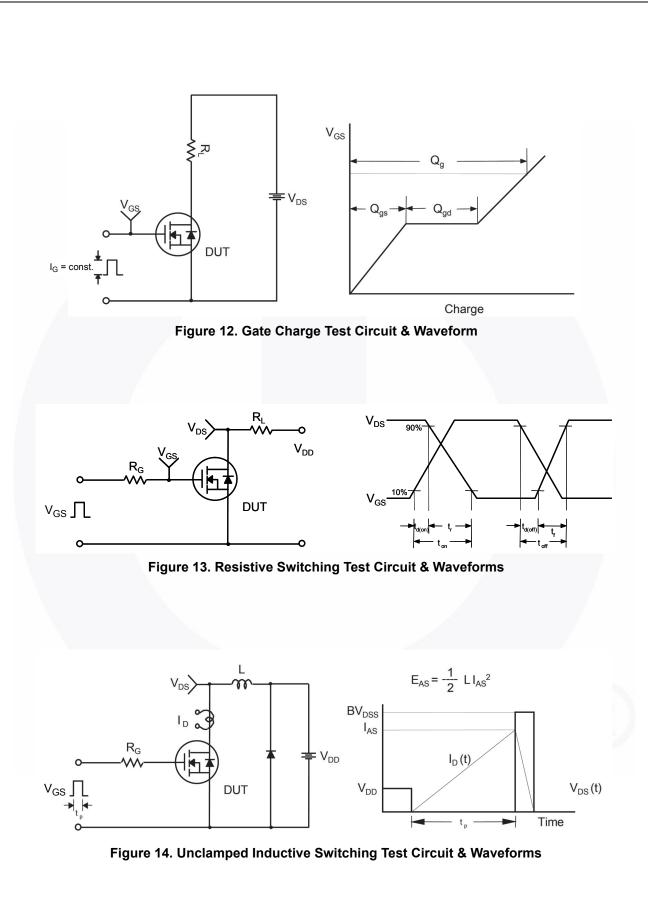
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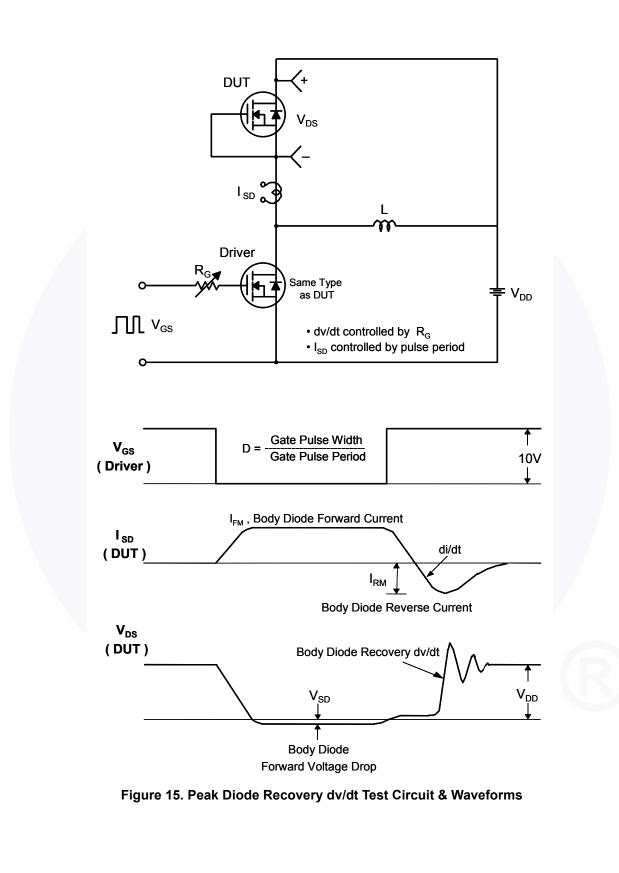
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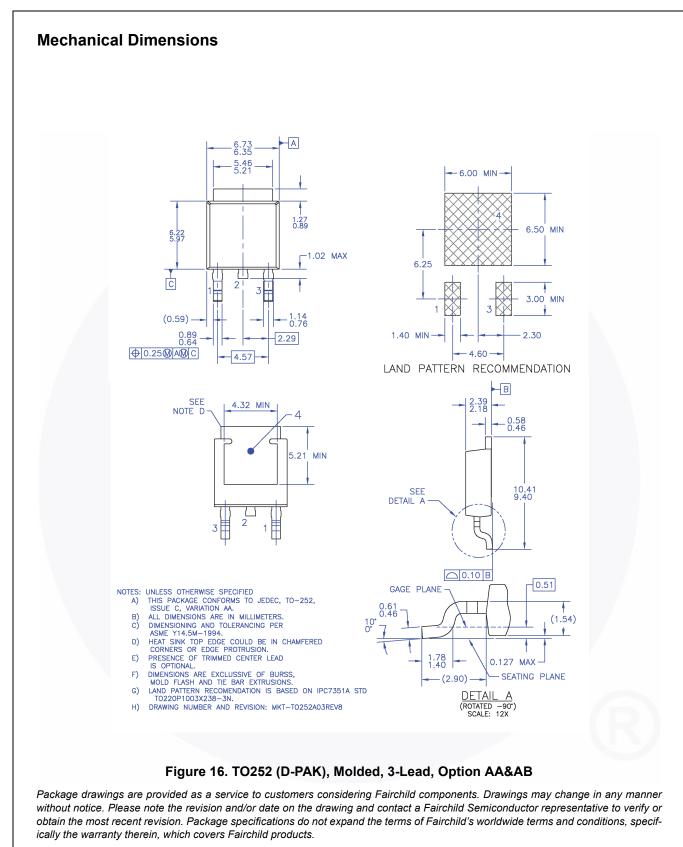




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